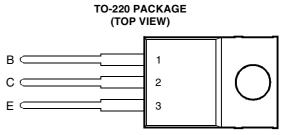
BOURNS®

BD540, BD540A, BD540B, BD540C PNP SILICON POWER TRANSISTORS

- Designed for Complementary Use with the BD539 Series
- 45 W at 25°C Case Temperature
- 5 A Continuous Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

| RATING | SYMBOL | VALUE | UNIT | |
|--|------------------|------------------|-------------|----|
| | BD540 | | -40 | |
| Collector-base voltage $(I_{F} = 0)$ | BD540A | V | -60 | v |
| $Collector-base voltage (I_{E} = 0)$ | BD540B | V _{CBO} | -80 | v |
| | BD540C | | -100 | |
| | BD540 | | -40 | |
| $O_{\rm eff}$ | BD540A | V | -60 | V |
| Collector-emitter voltage $(I_B = 0)$ (see Note 1) | BD540B | V _{CEO} | -80 | |
| | BD540C | | -100 | |
| Emitter-base voltage | V _{EBO} | -5 | V | |
| Continuous collector current | Ι _C | -5 | А | |
| Continuous device dissipation at (or below) 25°C case temperature (see Note 2) | | | 45 | W |
| Continuous device dissipation at (or below) 25°C free air temperature (see Note 3) | | | 2 | W |
| Operating free air temperature range | | | -65 to +150 | °C |
| Operating junction temperature range | Тj | -65 to +150 | °C | |
| Storage temperature range | T _{stg} | -65 to +150 | °C | |
| Lead temperature 3.2 mm from case for 10 seconds | TL | 260 | °C | |

NOTES: 1. These values apply when the base-emitter diode is open circuited.

2. Derate linearly to 150°C case temperature at the rate of 0.36 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

PRODUCT INFORMATION

BD540, BD540A, BD540B, BD540C PNP SILICON POWER TRANSISTORS



electrical characteristics at 25°C case temperature

| PARAMETER | | | TEST CONDITION | ONS | ТҮР | MAX | UNIT | |
|----------------------|--|---|-------------------------|---------------------|------|-----|-------|----|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C = -30 mA (see Note 4) | | BD540 | -40 | | | |
| | | | I _B = 0 | BD540A | -60 | | | v |
| | | | | BD540B | -80 | | | |
| | | | | BD540C | -100 | | | |
| | Collector-emitter cut-off current | $V_{CE} = -40 V$ | $V_{BE} = 0$ | BD540 | | | -0.2 | mA |
| 1 | | V _{CE} = -60 V | $V_{BE} = 0$ | BD540A | | | -0.2 | |
| ICES | | V _{CE} = -80 V | $V_{BE} = 0$ | BD540B | | | -0.2 | |
| | | V _{CE} = -100 V | $V_{BE} = 0$ | BD540C | | | -0.2 | |
| | Collector cut-off | V _{CE} = -30 V | I _B = 0 | BD540/540A | | | -0.3 | mA |
| I _{CEO} | current | V _{CE} = -60 V | I _B = 0 | BD540B/540C | | | -0.3 | ША |
| I _{EBO} | Emitter cut-off current | V _{EB} = -5 V | I _C = 0 | | | | -1 | mA |
| | Forward current transfer ratio | $V_{CE} = -4 V$ | I _C = -0.5 A | | 40 | | | |
| h _{FE} | | $V_{CE} = -4 V$ | I _C = -1 A | (see Notes 4 and 5) | 30 | | | |
| | | $V_{CE} = -4 V$ | | | 12 | | | |
| | Collector-emitter saturation voltage | I _B = -125 mA | I _C = -1A | | | | -0.25 | |
| V _{CE(sat)} | | I _B = -375 mA | I _C = -3 A | (see Notes 4 and 5) | | | -0.8 | V |
| | | I _B = -1 A | I _C = - 5A | | | | -1.5 | |
| V _{BE} | Base-emitter voltage | V _{CE} = -4 V | I _C = -3 A | (see Notes 4 and 5) | | | -1.25 | V |
| h _{fe} | Small signal forward current transfer ratio | V _{CE} = -10 V | I _C = -0.5 A | f = 1 kHz | 20 | | | |
| h _{fe} | Small signal forward current transfer ratio | V _{CE} = -10 V | I _C = -0.5 A | f = 1 MHz | 3 | | | |

NOTES: 4. These parameters must be measured using pulse techniques, $t_p = 300 \ \mu s$, duty cycle $\leq 2\%$.

5. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

| PARAMETER | | | ТҮР | MAX | UNIT |
|-----------------|---|--|-----|------|------|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 2.78 | °C/W |
| R_{\thetaJA} | Junction to free air thermal resistance | | | 62.5 | °C/W |

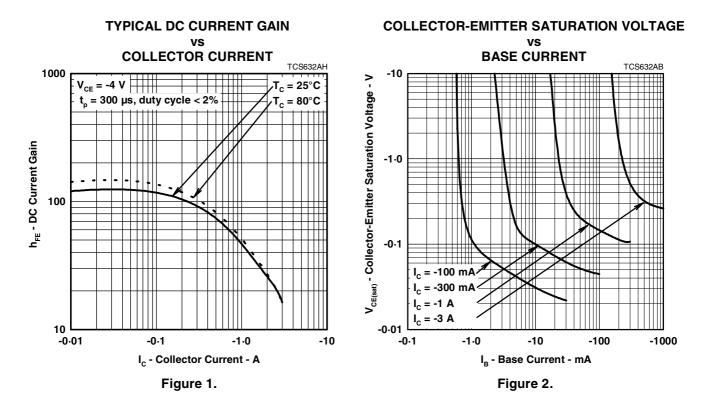
resistive-load-switching characteristics at 25°C case temperature

| | PARAMETER | TEST CONDITIONS [†] | | | MIN | ТҮР | MAX | UNIT |
|------------------|---------------|------------------------------|-----------------------------|-----------------------------|-----|-----|-----|------|
| t _{on} | Turn-on time | I _C = -1 A | I _{B(on)} = -0.1 A | $I_{B(off)} = 0.1 A$ | | 0.3 | | μs |
| t _{off} | Turn-off time | $V_{BE(off)} = 4.3 V$ | $R_L = 30 \ \Omega$ | t_p = 20 µs, dc \leq 2% | | 1 | | μs |

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.



TYPICAL CHARACTERISTICS



BASE-EMITTER VOLTAGE vs **COLLECTOR CURRENT** TCS632AC -1 $V_{CE} = -4 V$ $T_c = 25^{\circ}C$ V_{BE} - Base-Emitter Voltage - V -0.9 -0.8 -0.7 -0.6 -0.5 -0.01 -0.1 -1 -10 I_c - Collector Current - A Figure 3.

PRODUCT INFORMATION

JUNE 1973 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.

MAXIMUM SAFE OPERATING REGIONS

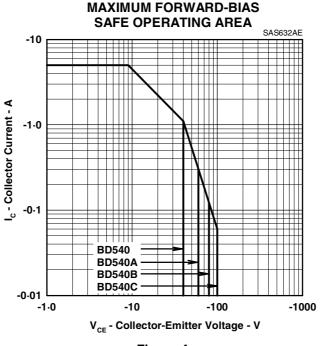
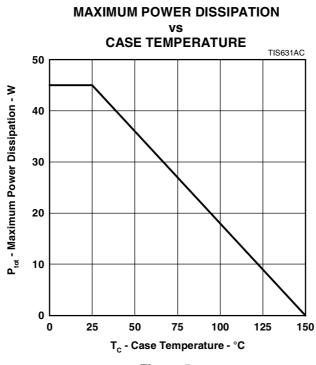


Figure 4.







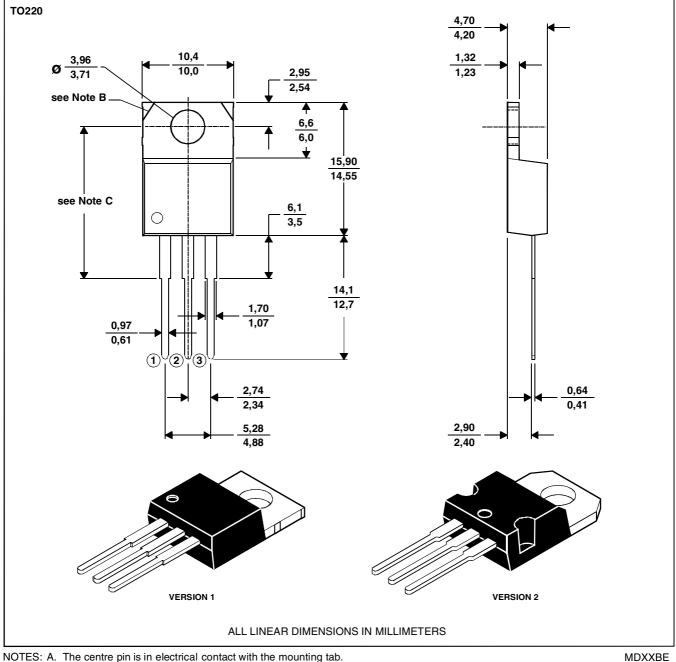
PRODUCT INFORMATION

MECHANICAL DATA

TO-220

3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



B. Mounting tab corner profile according to package version.

C. Typical fixing hole centre stand off height according to package version. Version 1, 18.0 mm. Version 2, 17.6 mm.

PRODUCT INFORMATION

JUNE 1973 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.